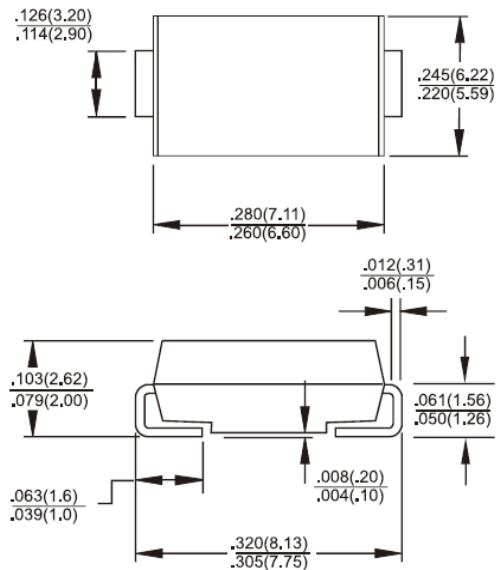


**SMC/DO-214AB**

**Features**

- ✧ For surface mounted application
- ✧ Glass passivated junction chip.
- ✧ Low forward voltage drop
- ✧ High current capability
- ✧ Easy pick and place
- ✧ High surge current capability
- ✧ Plastic material used carries Underwriters Laboratory Classification 94V-0
- ✧ High temperature soldering: 260°C/10 seconds at terminals
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode.


**Dimensions in inches and (millimeters)**
**Marking Diagram**


- S4X = Specific Device Code
- G = Green Compound
- Y = Year
- M = Work Month

**Mechanical Data**

- ✧ Case: Molded plastic
- ✧ Terminals: Pure tin plated, lead free.
- ✧ Polarity: Indicated by cathode band
- ✧ Packaging: 16mm tape per EIA STD RS-481
- ✧ Weight: 0.21 grams

**Maximum Ratings and Electrical Characteristics**

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	S4A	S4B	S4D	S4G	S4J	S4K	S4M	Units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @ $T_L=75^\circ\text{C}$	$I_{F(AV)}$	4							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	$I_{FSM}$	100							A
Maximum Instantaneous Forward Voltage (Note 1) @ 4 A	$V_F$	1.15							V
Maximum DC Reverse Current @ $T_A=25^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_A=125^\circ\text{C}$	$I_R$	10 250							uA uA
Typical Reverse Recovery Time (Note 2)	$T_{rr}$	1.5							uS
Typical Junction Capacitance (Note 3)	$C_j$	60							pF
Typical Thermal Resistance	$R_{\theta JL}$ $R_{\theta JA}$	13 47							$^\circ\text{C/W}$
Operating Temperature Range	$T_J$	- 55 to + 150							$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	- 55 to + 150							$^\circ\text{C}$

Notes: 1. Pulse Test with PW=300 usec, 1% Duty Cycle

 2. Reverse Recovery Test Conditions:  $I_F=0.5\text{A}$ ,  $I_R=1.0\text{A}$ ,  $I_{RR}=0.25\text{A}$ 

 3. Measured at 1 MHz and Applied  $V_R=4.0$  Volts

## RATINGS AND CHARACTERISTIC CURVES (S4A THRU S4M)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

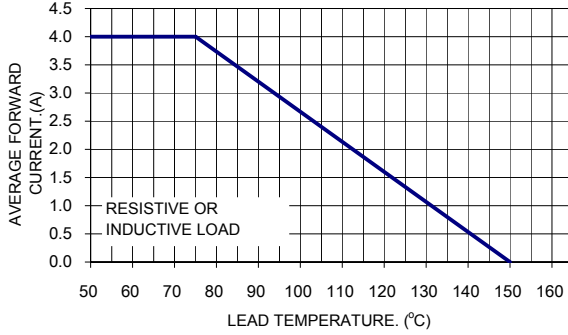


FIG.2- TYPICAL REVERSE CHARACTERISTICS

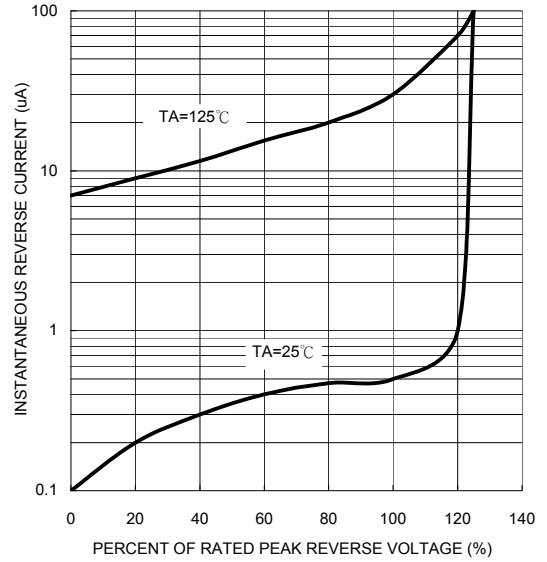


FIG.3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

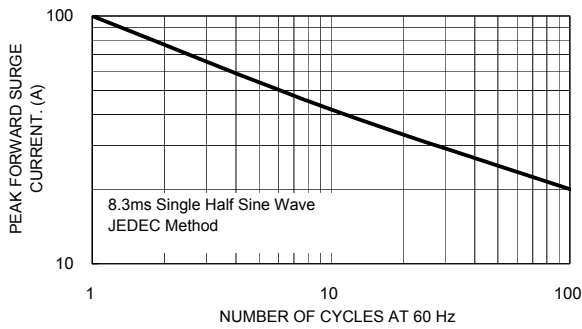


FIG.5- TYPICAL FORWARD CHARACTERISTICS

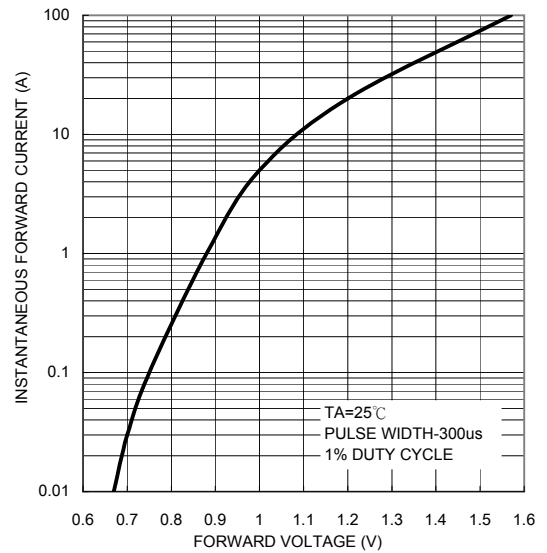


FIG.4- TYPICAL JUNCTION CAPACITANCE

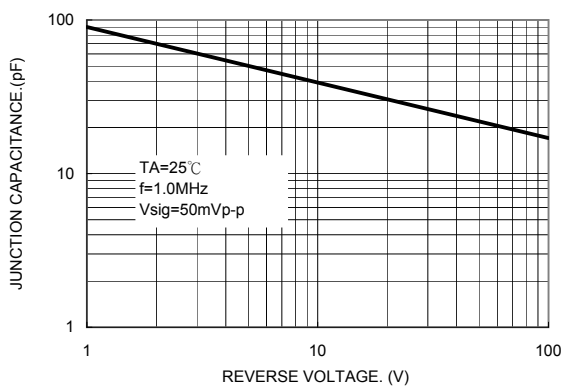
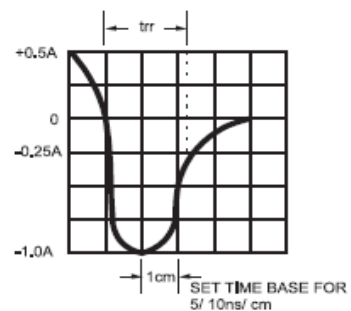
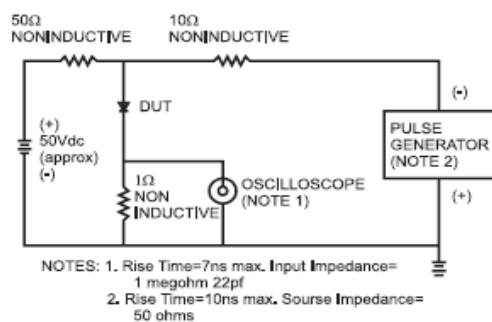


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [Schottky Diodes & Rectifiers](#) category:*

*Click to view products by [Taiwan Semiconductor](#) manufacturer:*

Other Similar products are found below :

[CUS06\(TE85L,Q,M\)](#) [MA4E2039](#) [D1FH3-5063](#) [MBR0530L-TP](#) [MBR10100CT-BP](#) [MBR30H100MFST1G](#) [MMBD301M3T5G](#) [PMAD1103-LF](#) [PMAD1108-LF](#) [RB160M-50TR](#) [RB520S-30](#) [RB551V-30](#) [DD350N18K](#) [DZ435N40K](#) [DZ600N16K](#) [BAS16E6433HTMA1](#) [BAS 3010S-02LRH E6327](#) [BAT 54-02LRH E6327](#) [IDL02G65C5XUMA1](#) [NSR05F40QNXT5G](#) [NSVR05F40NXT5G](#) [JANS1N6640](#) [SB07-03C-TB-H](#) [SB1003M3-TL-W](#) [SBAT54CWT1G](#) [SBM30-03-TR-E](#) [SBS818-TL-E](#) [SK32A-LTP](#) [SK33A-TP](#) [SK34A-TP](#) [SK34B-TP](#) [SMD1200PL-TP](#) [ACDBN160-HF](#) [SS3003CH-TL-E](#) [STPS30S45CW](#) [PDS3100Q-7](#) [GA01SHT18](#) [CRS10I30A\(TE85L,QM\)](#) [MBR1240MFST1G](#) [MBRB30H30CT-1G](#) [BAS28E6433HTMA1](#) [BAS 70-02L E6327](#) [HSB123JTR-E](#) [JANTX1N5712-1](#) [VS-STPS40L45CW-N3](#) [DD350N12K](#) [SB007-03C-TB-E](#) [SB10015M-TL-E](#) [SB1003M3-TL-E](#) [SK110-LTP](#)